

Table 1: Lab 4 Comparisons

Element	Measured	Simulated	Percent Differences
V_1	15.478 [V]	15.837 [V]	2.2668 %
V_2	11.478 [V]	12.273 [V]	6.4776 %
V_3	13.897 [V]	14.008 [V]	0.7924 %
V_4	18.032 [V]	18.034 [V]	0.0111 %
V_S	18.034 [V]	18.034 [V]	0 %
I_1	15.307 [mA]	15.979 [mA]	4.2055 %
I_2	26.36 [mA]	27.093 [mA]	2.7055 %
I_3	2.428 [mA]	2.5925 [mA]	6.3452 %
I_4	8.167 [mA]	8.5218 [mA]	4.1634 %
I_5	9.394 [mA]	9.4264 [mA]	0.3437 %
I_6	11.607 [mA]	12.019 [mA]	3.4279 %
I_7	18.664 [mA]	18.688 [mA]	0.1284 %
I_S	15.979 [mA]	15.979 [mA]	0 %
$I_V S$	38.59 [mA]	39.229 [mA]	1.6289 %
R_1	52.25 [mW]	56.938 [mW]	8.2335 %
R_2	314.767 [mW]	332.52 [mW]	5.3389 %
R_3	3.944 [mW]	4.4964 [mW]	12.2854 %
R_4	45.089 [mW]	49.092 [mW]	8.1541 %
R_5	131.135 [mW]	132.04 [mW]	0.6854 %
R_6	45.132 [mW]	48.392 [mW]	6.7367 %
R_7	336.156 [mW]	337.02 [mW]	0.2564 %
I_S	247.323 [mW]	253.05 [mW]	2.2632 %
V_S	695.932 [mW]	707.45 [mW]	1.6281 %

Table 2: Lab 5 Comparisons			
Element	Measured	Simulated	Percent Differences
V_E	1.139 [V]	1.0514 [V]	8.331748145 %
V_C	11.335 [V]	11.587 [V]	2.174851126 %
V_B	1.995 [V]	1.7539 [V]	13.74650778 %
V_{CC}	16 [V]	16 [V]	0 %
I_S	10.07 [mA]	9.6458 [mA]	4.397768977 %
I_C	9.997 [mA]	9.5718 [mA]	4.442215675 %
I_E	0.0575 [mA]	0.074 [mA]	22.34556897 %
I_B	10.447 [mA]	10.101 [mA]	3.425403425 %
R_C	11.0531 [mW]	10.142 [mW]	8.983771445 %
R_E	46.0723 [mW]	42.236 [mW]	9.083114284 %
V_{CC}	110.0265 [mW]	100.9 [mW]	9.04511571 %
<i>Transistor</i>	-167.152 [mW]	-161.62 [mW]	3.422843707 %